

GSE120BB1D3F

ESD Protection Diode

Product Description

It is designed to protect sensitive electronics from damage due to electrostatic discharge (ESD) and other transient events.

Features

- Operating Voltage: 12V
- IEC61000-4-2(ESD) $\pm 30\text{kV}$ (Air)
- IEC61000-4-2(ESD) $\pm 30\text{kV}$ (Contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns).
- IEC61000-4-5 (Lightning) 12A (8/20 μs).



Mechanical Data

- SOD-323. Package
- RoHS Compliant and Halogen Free

Package and Pin Assignment

SOD-323	Equivalent Circuit
	

Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSE120BB1D3F	SOD-323	AB 	3,000PCS
GSE120BB1D3F - Product Code: GSE120BB1 - Package Code: D3 for SOD-323 - Green Level: F for RoHS Compliant and Halogen Free			
Marking Information			
		- Product Code: AB - GS Code: <input type="checkbox"/> <input type="checkbox"/>	

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
P _{PP}	Peak Pulse Power (t _p =8/20μs)	350	W
I _{PP}	Peak Pulse Current (t _p =8/20μs)	12	A
V _{ESD}	ESD Per IEC61000-4-2 (Air)	±30	KV
	ESD Per IEC61000-4-2 (Contact)	±30	KV
T _J	Operating Junction Temperature Range	-55 to +125	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	-			12	V
V _{BR}	Breakdown Voltage	I _T = 1mA	13.3			V
I _R	Reverse Leakage Current	V _{RWM} =12V			1	μA
V _C	Clamping Voltage	I _{PP} =1A (8/20μs)			19	V
		I _{PP} =12A (8/20μs)			28.6	V
C _J	Junction Capacitance	V _R =0V, f=1MHz		0.8		pF

Electrical Parameters

Symbol	Parameter	
I _{PP}	Reverse Peak Pulse Current	
V _C	Clamping Voltage @ I _{PP}	
V _{RWM}	Reverse Stand-Off Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
I _T	Test Current	

Typical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

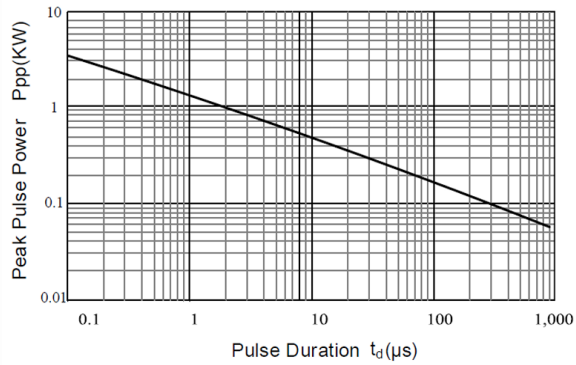


Fig 1. Peak Pulse Power vs. Pulse Time

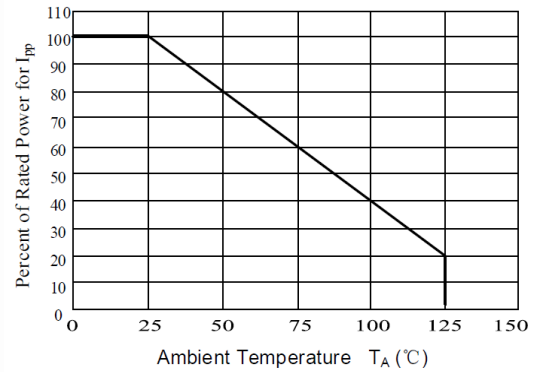


Fig 2. Power Derating Curve

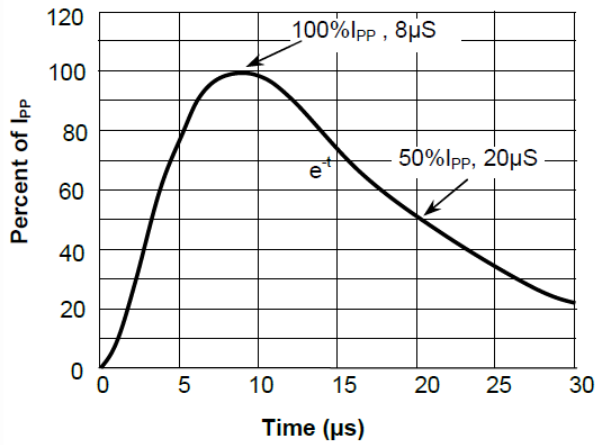


Fig 3. 8 X 20 μs Pulse Waveform

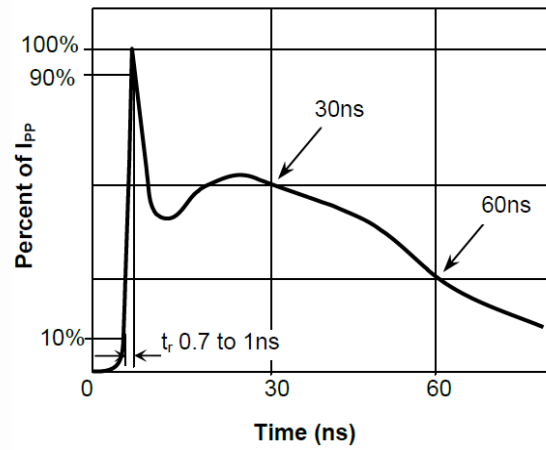
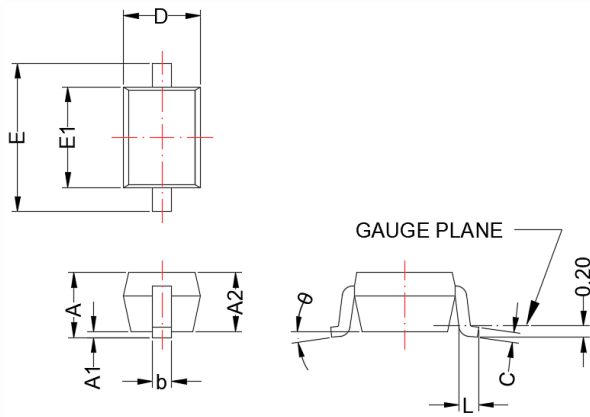


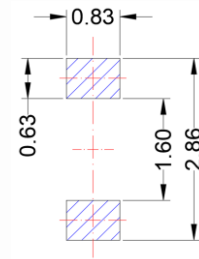
Fig 4. ESD(IEC61000-4-2) Pulse Waveform

SOD-323

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	---	1.16	---	0.046
A1	0.00	0.14	0.000	0.006
A2	0.80	---	0.031	---
b	0.25	0.40	0.010	0.016
C	0.08	0.25	0.003	0.010
D	1.15	1.40	0.045	0.055
E	2.30	2.80	0.091	0.110
E1	1.40	1.80	0.055	0.071
L	0.08	---	0.003	---
θ	0°	8°	0°	8°





NOTE:



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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CONTACT US

GS Headquarter	
	4F, NO.43-1, Lane 11, Sec. 6, Minquan E. Rd Neihu District, Taipei City 114761, Taiwan (R.O.C).
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587